### DISCRETE SEMICONDUCTORS

# DATA SHEET

**PEMB13**; **PUMB13** PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

Product specification Supersedes data of 2003 Dec 11 2004 Apr 15





 $\mathsf{k}\Omega$ 

# PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

PEMB13; PUMB13

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### **APPLICATIONS**

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

	SYMBOL	PARAMETER	TYP.	MAX.	UNIT
	$V_{CEO}$	collector-emitter voltage	_	<b>-50</b>	>
ŀ	I <sub>O</sub>	output current (DC)	_	-100	mA
Ī	TR1	PNP	_	-	-
Ī	TR2	PNP	_	_	_
Ī	R1	bias resistor	4.7	_	kΩ

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**QUICK REFERENCE DATA** 

bias resistor

#### **DESCRIPTION**

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PACE	(AGE	MARKING CODE NPN/PNP		NPN/NPN
I TPE NOMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMB13	SOT666	_	45	PEMD13	PEMH13
PUMB13	SOT363	SC-88	B*5	PUMD13	PUMH13

R2

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
I TPE NUMBER	SIMIPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION	
PEMB13	6 5 4	1	emitter TR1	
PUMB13	6 5 4	2	base TR1	
	R1 R2	3	collector TR2	
	TR2	4	emitter TR2	
	TR1	5	base TR2	
		6	collector TR1	
	1 2 3			
	1 2 3 Top view MAM477			

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### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE		
I TPE NOWIBER	NAME	DESCRIPTION	VERSION	
PEMB13	_	plastic surface mounted package; 6 leads		
PUMB13	_	plastic surface mounted package; 6 leads SOT36		

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+5	V
	negative		_	-30	V
Io	output current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device	<b>;</b>	•		•	•
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	_	300	mW

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0$	_	_	-170	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	100	_	_	
V <sub>CEsat</sub>	saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-100	mV
$V_{i(off)}$	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-0.6	-0.5	V
V <sub>i(on)</sub>	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-1.3	-0.9	_	V
R1	input resistor		3.3	4.7	6.1	kΩ
R2 R1	resistor ratio		8	10	12	
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	pF

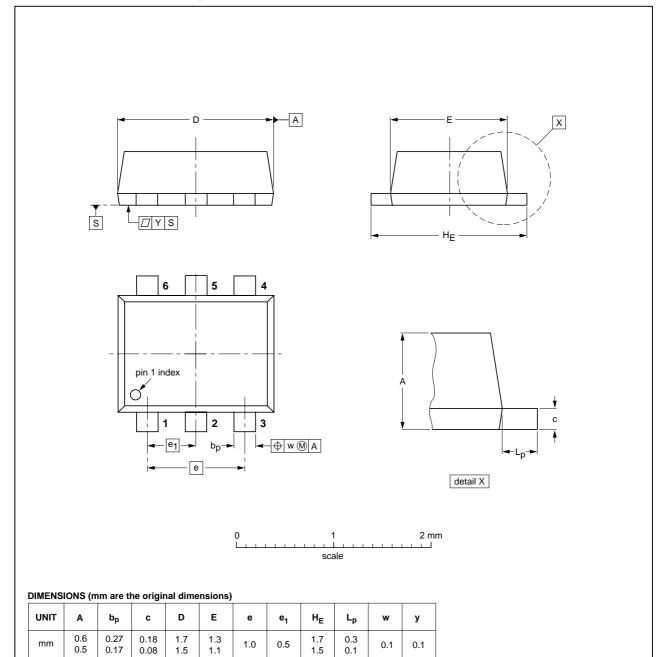
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#### **PACKAGE OUTLINES**

### Plastic surface mounted package; 6 leads

SOT666



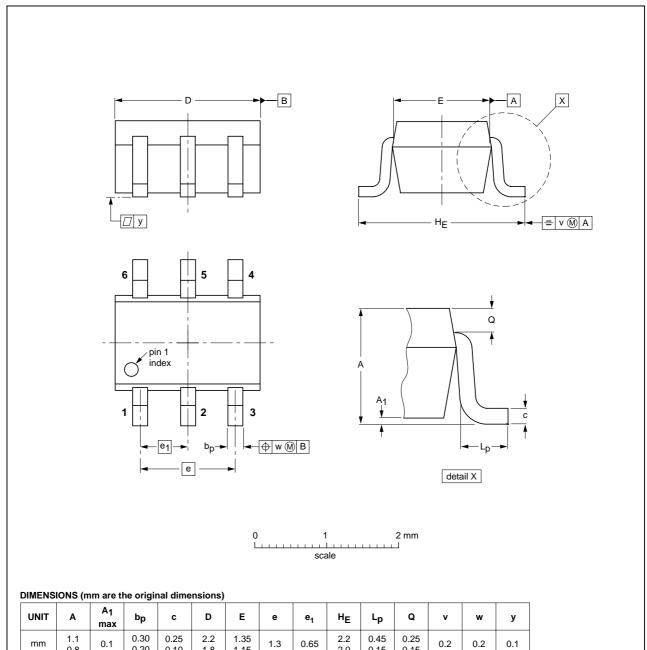
OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT666						<del>-01-01-04</del> 01-08-27	

## PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

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### Plastic surface mounted package; 6 leads

**SOT363** 



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT363			SC-88			97-02-28	

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### PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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